

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1234	235/494.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:49
L2	364	355/43.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:49
L3	2879	355/53.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:49
L4	108	430/13.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:49
L5	558	257/620.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:49
L6	4	((code\$1 or mark\$1) near10 (inside\$1 or wall\$1) near20 notch\$2) same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:50
L7	223	((((355/53.ccls. and semiconductor) and wafer) and mark) and identical	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:51
L8	6875	(semiconductor adj wafer) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:51
L9	640	(code\$1 or mark\$1) same first same second same wafer same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:51
L10	1249	replace same mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:51

L11	129	(replace same mark) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:51
L12	1	(replace same mark) and semiconductor same identification	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/24 15:52
S1	1207	235/494.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:21
S2	2666	355/53.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:23
S3	364	355/43.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:23
S4	108	430/13.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:24
S5	530	257/620.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:31
S6	605	(code\$1 or mark\$1) same first same second same wafer same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:31
S7	9	(code\$1 or mark\$1) same first same second same wafer same semiconductor same notch\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:31
S8	3	((code\$1 or mark\$1) near10 (inside\$1 or wall\$1) near20 notch\$2) same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:32

S9	2	"20040129940"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:34
S10	2	"5147824".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:35
S11	2	"20030015806"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 15:41
S12	0	"20030015806".URPN.	USPAT	OR	OFF	2004/08/06 15:35
S13	6	"4418467".pn. "5028200".pn. "6120607".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 16:10
S14	10	((("4547446") or ("4327292") or ("6120607") or ("4701050") or ("6277658") or ("6268641") or ("6004405") or ("5907144") or ("5876819") or ("4418467"))).PN.	USPAT; USOCR	OR	OFF	2004/08/06 16:12
S15	10	((("4547446") or ("4327292") or ("6120607") or ("4701050") or ("6277658") or ("6268641") or ("6004405") or ("5907144") or ("5876819") or ("4418467"))).PN.	USPAT; USOCR	OR	OFF	2004/08/06 16:29
S16	17105	chiba.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 16:29
S17	942	S16 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 16:29
S18	22	S17 and notch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 16:29
S19	7	S18 and marking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 17:50

S20	4	"6268641".pn. "6312876".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/06 17:50
S21	0	235/494.ccls. and chiba.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 17:56
S22	0	jp-223380-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 17:56
S23	9	"223380"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 17:57
S24	0	jp-223380-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 17:58
S25	0	jp-5923512-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 17:58
S26	2	jp-2000223380-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:00
S27	0	jp-2175154-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:00
S28	1	jp-3116919-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:00
S29	15423	chiba.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:02

S30	818	chiba.in. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:02
S31	58	(chiba.in. and semiconductor) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:05
S32	153	(chiba.in. and semiconductor) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:06
S33	83	235/494.ccls. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:10
S34	8	(235/494.ccls. and semiconductor) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:06
S35	34	(235/494.ccls. and semiconductor) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:47
S36	2	"6305677".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:16
S37	174	269/13.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:18
S38	81423	semiconductor adj2 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:19
S39	4744	(semiconductor adj2 wafer) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:19

S40	4500	((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:20
S41	61	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:53
S42	22	semiconductor adj mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:52
S43	1154	355/53.ccls. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:29
S44	1052	(355/53.ccls. and semiconductor) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:29
S45	415	((355/53.ccls. and semiconductor) and wafer) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:30
S46	8	((((355/53.ccls. and semiconductor) and wafer) and mark) and reproduce	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:32
S47	0	((((355/53.ccls. and semiconductor) and wafer) and mark) and efface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:32
S48	5	((((355/53.ccls. and semiconductor) and wafer) and mark) and erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:34
S49	0	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce adj erased adj marks)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:35

S50	0	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and efface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:35
S51	10	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks)) and notch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:35
S52	300	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce erased marks))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:38
S53	0	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce near erased near marks))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:39
S54	0	((((355/53.ccls. and semiconductor) and wafer) and mark) and (reproduce same erased same marks))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:39
S55	121	((((355/53.ccls. and semiconductor) and wafer) and mark) and identical	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:40
S56	9	((((355/53.ccls. and semiconductor) and wafer) and mark) and identical) and reproduce\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:44
S57	172	((((355/53.ccls. and semiconductor) and wafer) and mark) and prevent	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:44
S58	3	((((355/53.ccls. and semiconductor) and wafer) and mark) and prevent) and erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:53
S59	354	355/43.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:53

S60	84	355/43.ccls. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:53
S61	71	(355/43.ccls. and semiconductor) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:53
S62	1	((355/43.ccls. and semiconductor) and wafer) and mark) and erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:54
S63	45	((355/43.ccls. and semiconductor) and wafer) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:58
S64	25968	"355"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:58
S65	2116	"355"/\$.ccls. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:59
S66	1469	("355"/\$.ccls. and semiconductor) and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:59
S67	497	((("355"/\$.ccls. and semiconductor) and wafer) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:59
S68	8	((("355"/\$.ccls. and semiconductor) and wafer) and mark) and erase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 18:59
S69	13	((("355"/\$.ccls. and semiconductor) and wafer) and mark) and reproduce	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 19:02



S70	1	((("355"/\$.ccls. and semiconductor) and wafer) and mark) and erase) and ((("355"/\$.ccls. and semiconductor) and wafer) and mark) and reproduce)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/30 19:02
S71	6	(235/494.ccls. and semiconductor) and mark and duplicate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:51
S72	0	(235/494.ccls. and semiconductor) and (duplicate adj mark)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:51
S73	3	(235/494.ccls. and semiconductor) and (duplicate same mark)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:51
S74	0	(semiconductor adj mark) same duplicate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:53
S75	0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce ) and (duplicate same mark)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:53
S76	0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce ) and (duplicate near mark)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:53
S77	0	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce ) and (duplicate adj mark)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:53
S78	72	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:54
S79	3	((((semiconductor adj2 wafer) and mark) and (semiconductor adj wafer)) and reproduce ) and duplicate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/09 18:54

S80	26645	"355"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/10 12:08
S81	102	430/13.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/10 12:09
S82	435	257/620.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/01/10 12:09
S83	1104	235/494.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:08
S84	27013	"355"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:08
S85	462	257/620.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:09
S86	104	430/13.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:09
S87	1015	replace same mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:09
S88	99	(replace same mark) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:12
S89	3	((replace same mark) and semiconductor) and "235"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:14

S90	89611	semiconductor adj wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:19
S91	5456	(semiconductor adj wafer) and mark	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:20
S92	2	((semiconductor adj wafer) and mark) and (replace near10 mark)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/05/30 12:20